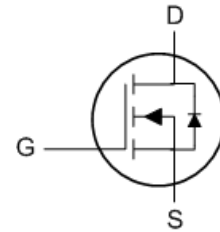




- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

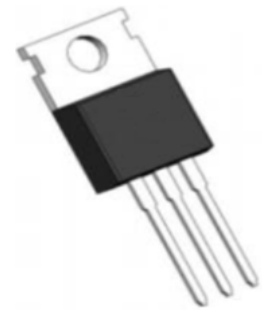


Description

The WLP100N02 is the high cell density trenched N-ch MOSFETs, which provide excellent R_{DS(on)} and gate charge for most of the synchronous buck converter applications.

The WLP100N02 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO220AB Pin Configuration



Product Summary

BVDSS	R _{DS(on)}	I _D
20V	2.7mΩ	100A

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	20	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	100	A
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	59	A
I _{DM}	Pulsed Drain Current ²	360	A
EAS	Single Pulse Avalanche Energy ³	118	mJ
I _{AS}	Avalanche Current	41	A
P _D @T _C =25°C	Total Power Dissipation ⁴	88	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJC}	Thermal Resistance Junction-Case ¹	---	1.8	°C/W



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	---	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=4.5V, I_D=30A$	---	2.7	4	m Ω
		$V_{GS}=2.5V, I_D=20A$	---	4	6	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	0.4	0.7	1	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	$\text{mV}/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=20V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=20V, V_{GS}=0V, T_J=100^\circ\text{C}$	---	---	---	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 12V, V_{DS}=0V$	---	---	± 100	nA
gfs	Forward Transconductance	$V_{DS}=5V, I_D=20A$	---	---	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	---	---	Ω
Q_g	Total Gate Charge	$V_{DS}=10V, V_{GS}=4.5V, I_D=30A$	---	48	---	nC
Q_{gs}	Gate-Source Charge		---	3.6	---	
Q_{gd}	Gate-Drain Charge		---	19	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{GS}=4.5V, V_{DS}=10V, I_D=30A, R_{GEN}=1.8\Omega$	---	9.7	---	ns
T_r	Rise Time		---	37	---	
$T_{d(off)}$	Turn-Off Delay Time		---	63	---	
T_f	Fall Time		---	52	---	
C_{iss}	Input Capacitance	$V_{DS}=10V, V_{GS}=0V, f=1\text{MHz}$	---	3200	---	pF
C_{oss}	Output Capacitance		---	460	---	
C_{rss}	Reverse Transfer Capacitance		---	445	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	100	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=30A, T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=30A, di/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	23	---	nS
Q_{rr}	Reverse Recovery Charge		---	10	---	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: $T_J=25^\circ\text{C}$, $V_{DD}=15V$, $V_G=4.5V$, $R_G=25\Omega$, $L=0.5\text{mH}$, $I_{AS}=21A$

3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$



Typical Performance Characteristics

Figure 1: Output Characteristics

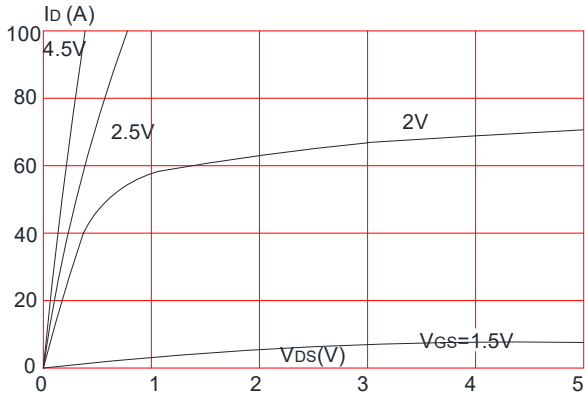


Figure 2: Typical Transfer Characteristics

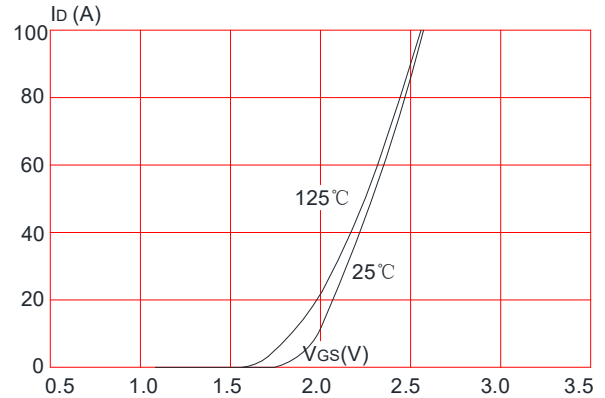


Figure 3: On-resistance vs. Drain Current

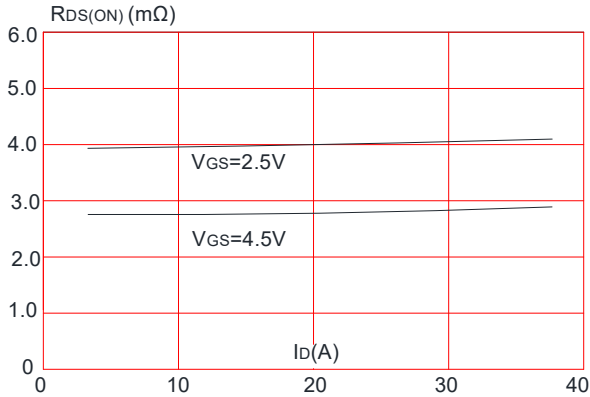


Figure 4: Body Diode Characteristics

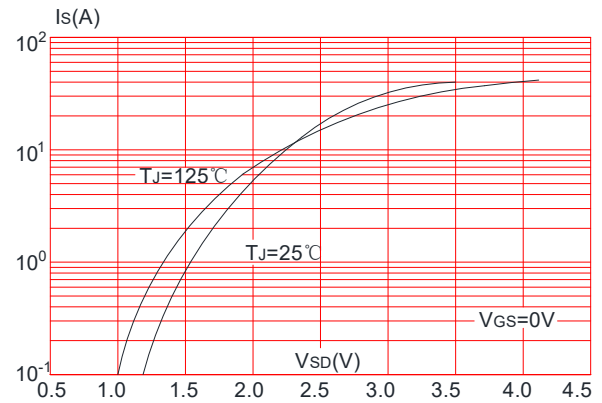


Figure 5: Gate Charge Characteristics

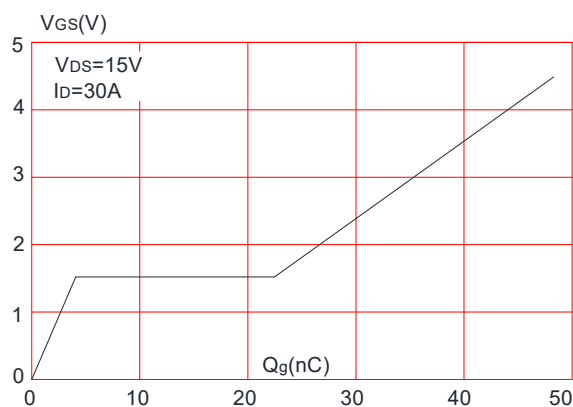


Figure 6: Capacitance Characteristics

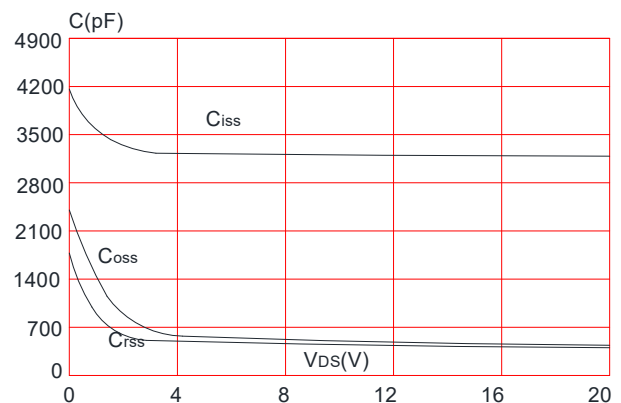




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

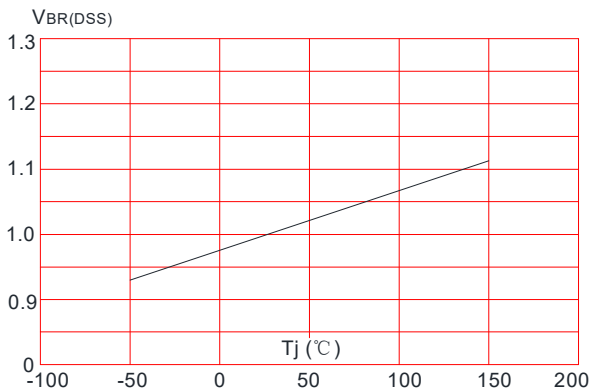


Figure 8: Normalized on Resistance vs. Junction Temperature

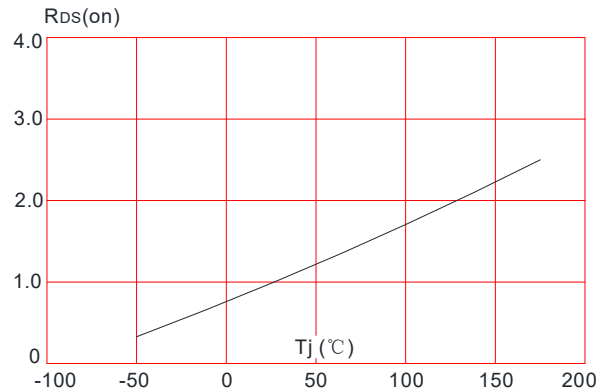


Figure 9: Maximum Safe Operating Area

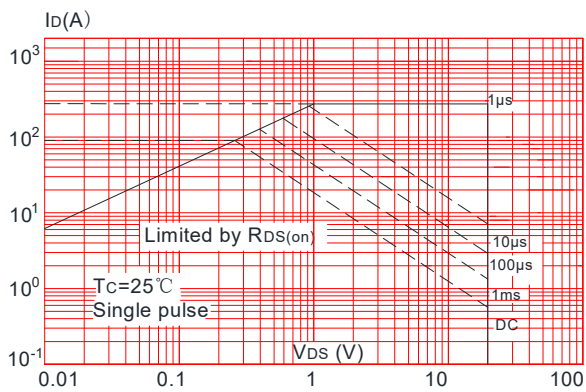


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

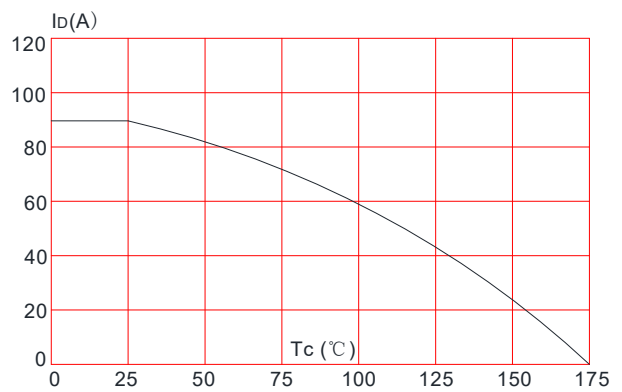
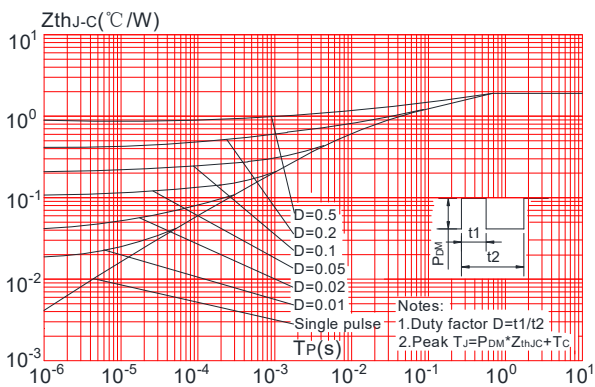


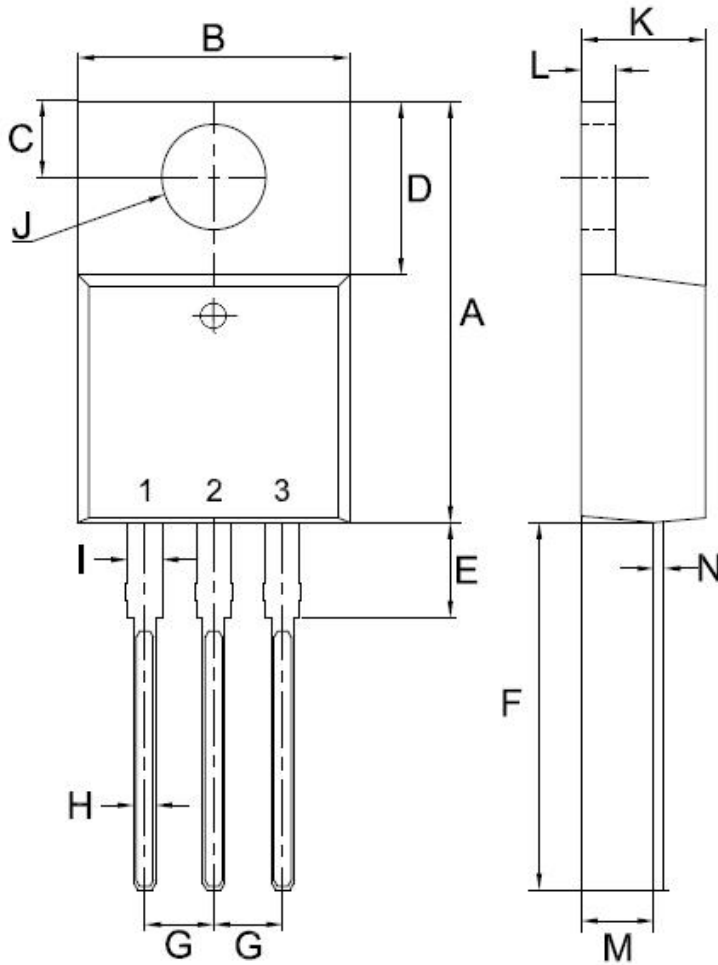
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case





Mechanical Dimensions for TO-220

COMMON DIMENSIONS



TO-220AB		
Unit:mm		
DIM	MIN	MAX
A	14.80	15.40
B	9.90	10.50
C	2.50	2.90
D	6.00	6.80
E	2.95	3.95
F	12.50	14.50
G	2.34	2.74
H	0.51	1.11
I	0.97	1.57
J	3.54 ϕ	4.14 ϕ
K	4.27	4.87
L	1.07	1.47
M	2.39	2.99
N	0.30	0.46



Disclaimer

Brunei has made reasonable commercial efforts to ensure that the information given in this datasheet is correct. However, it must clearly be understood that such information is for guidance only and does not constitute any representation or form part of any offer or contract.

For documents and material available from this datasheet, Brunei does not warrant or assume any legal liability or responsibility for the accuracy, completeness, or usefulness of any information, product, technology or process disclosed hereunder.

Brunei reserves the rights to at its own discretion to make any changes or improvements to this datasheet. Unless said datasheet is incorporated into the formal contract, any customer should not rely on the information as any specification or product parameters duly committed by Brunei Customers are hereby advised to verify that the information contained herein is current and complete before the entering of any contract or acknowledgement of any purchase order. Accordingly, all products specified hereunder shall be sold subject to Brunei's terms and conditions supplied at the time of order acknowledgement. Except where agreed upon by contractual agreement, testing of all parameters of each product is not necessarily performed.

Brunei does not warrant or convey any license either expressed or implied under its patent rights, nor the rights of others. Reproduction of information contained herein shall be only permissible if such reproduction is without any modification or alteration. Reproduction of this information with any alteration is an unfair and deceptive business practice. Brunei is not responsible or liable for such altered documentation.

Resale of Brunei's products with statements different from or beyond the parameters stated by Brunei for that product or service voids all express or implied warranties for the associated Brunei's product or service and is unfair and deceptive business practice. Brunei is not responsible or liable for any such statements.

Brunei's products are not authorized for use as critical components in life support devices or systems without the express written approval of Brunei. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform, when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.